Dielectrics and Capacitance ** Dielectrics

A diplocation:

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A diplocation is an insulating material that does not conduct predictive field.

The plocation more easily, diplocations have bound electrons that

cannot move dreply. However when placed in external electric field,

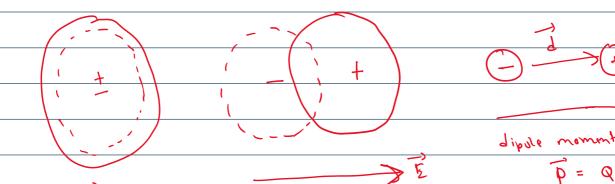
the charges within the diplocation recurrency Slightly Neading to

polorization.

Polarization

-> polarization reters to the alignment of electric dipoles within a dipoles within a dipoles material in response to an external electric field.

It occurs because the positive and negative charges shift sightly in apposite directions, creating dipoles within the material.



Unpolarized atom polarized atom

the positive charge is displaced in direction

Upon the application of electric field Elby the torce Fr = QE

Upon the application of electric field \vec{E}^{1} by the torce $\vec{F}_{1} = \vec{Q}\vec{E}$ while the negative charge is displaced in the apposite direction by the force $\vec{F}_{-} = \vec{Q}\vec{E}$. A dipole results from the displacement of charges, and the atom is said to be "polarized". This pheno menon is polarization. The direction of polarization is from '-' to 't' charges i.e in the direction of \vec{E} .

p (dipole moment) = qd (c-m)

where, G = positive one of the two bound charges composing the dipole J = vector from -ve to the charge

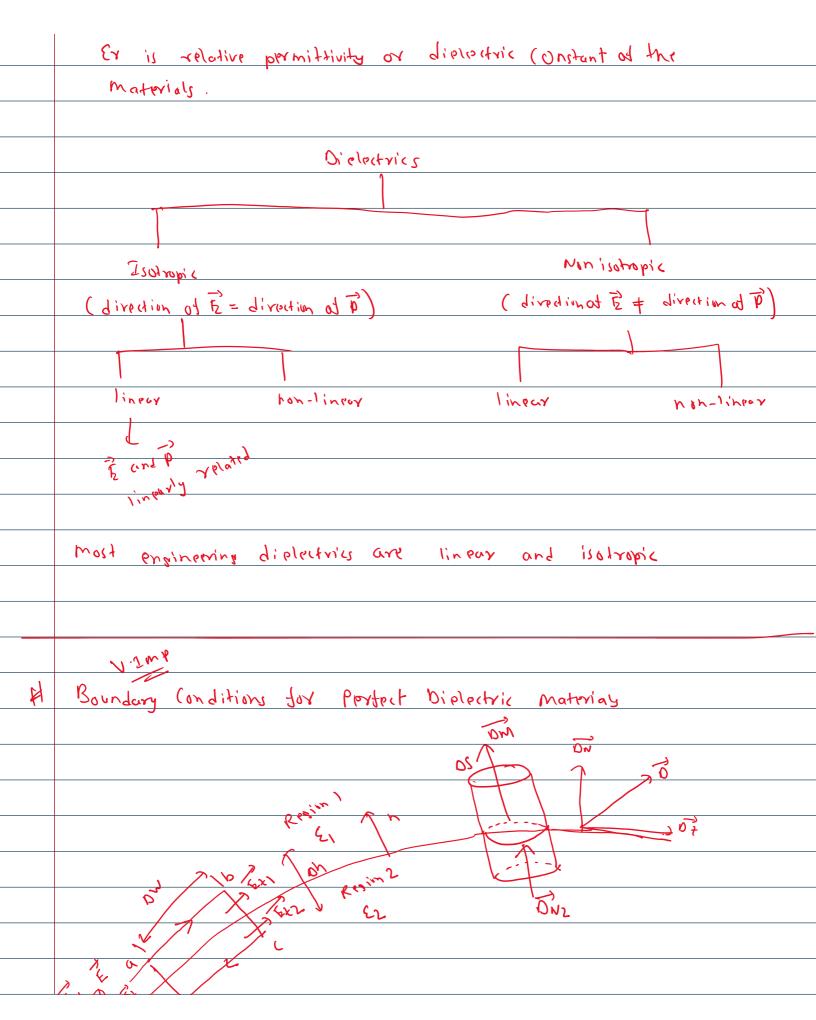
let n be the number of dipoles per unit volume, then there are nov dipoles in a volume DV. The total dipole moment is:

P total = Z P;

The polarization P is defined as the dipole moment per unit

Volume

*	Relationship between 0, E and P
	For iso tropic diploctric materials, the linear relationship between
	Pand E
	p = X & E (i)
	Le co e
	where Te (chi) is a dimensionless quantity (allow Plactric
	Susceptibility at the material
	≈ ou _l
	I is now destined in more general terms, as we are
	taking polarization in account,
	$D = \epsilon_0 E + P - cin$
	'
	Vsing ci) and cii)
	D= EOE + 7, EOE = (7,+1) EE
	1 0 - 80 E + 1) e 80 E - (1) e +1) co E
	which is in the form at D = EOEY E
	°0 [EY = √2] 00



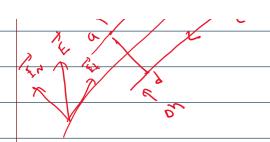


Fig: boundary condition between two pertect dielectric materials.

(onsider the interface between two dielectric having permittivities Exant Ez and occupying the region 1 and 2 as shown in Jigure.

For tongential components

$$\int_{\alpha}^{\infty} \frac{\vec{E} \cdot \vec{du}}{\vec{du}} + \int_{\alpha}^{\infty} \frac{\vec{E} \cdot \vec{du}}{\vec{du}} = 0$$

$$\text{MI EHOW} + 0 + (-E_{12} \text{ow}) + 0 = 0$$

$$\text{MON} = 0$$

which shows that the tangential component of the electric field intensity is continuous across the boundary.

Equation (i) may be writing as i

$\frac{0+1}{4} = \frac{0+2}{\epsilon_2}$
$\frac{\delta r_1}{c_2} = \frac{\epsilon_1}{c_2} \frac{\delta k_2}{c_2}$
ζ2
which mouns that the tangential component at electric flux density
is discontinuous across the boundary.
For horner component
\$ \(\frac{1}{2} \cdot 1
1 (D. 9) + (D. 9) = 00
1 top Oboston Jrige
N = N = 0 A =
$o_1 D_{V_1} \circ S - D_{V_2} \circ S + O = S_S \circ S$
$(\ \ \Diamond\ / \to \emptyset)$
of DN1 - DN2 = Ss
It no trep charge exist at interface (i.e charges are not
deliberately placed there), Ss = 0
DN1 - DN2 = 0
ON DW = DW (ii)
+ /
This shows that the normal component of electric flux density is
V V V V V V V V V V V V V V V V V V V

This shows that the normal component of electric flux density is
crntinuous
(quation (ii) ma be written a
EIENI = ESENS
$\frac{\mathcal{E}_{1} \mathcal{E}_{N_{1}}}{\mathcal{E}_{N_{1}}} = \frac{\mathcal{E}_{2} \mathcal{E}_{N_{2}}}{\mathcal{E}_{1}}$
Which means that the horman compat objective field intensity is
discordingow.
John John
0+1
(ξ_1) (ξ_1) (ξ_1)
retraction at D at a dielectric intertace
We know
DNI = DW 2
(M) P) (050) = P2 (0502
$\frac{b_2}{b_1} = \frac{(0/6)}{(0/6)} = \frac{(0/6)}{(0/6)}$
tangential comp discentingon

	$b_{t_1} = \frac{\varepsilon_t}{\varepsilon_2} b_{t_2}$
	on DH - CI
	οη <u>D</u> Η = <u>ει</u> P + ι ε ι
	$\frac{D_{2} \sin \theta_{2}}{D_{1} \sin \theta_{2}} = \frac{\epsilon_{1}}{\epsilon_{2}} \qquad (ii)$
	From cill and (i) (put b) and be from ci)
	(osessine) - c.
	$\frac{(osessine)}{coselsines} = \frac{\epsilon_1}{\epsilon_2}$
	trin 81 C
	tunoz Ez
	$C_1 \supset E_2 + cno_1 \supset tanb2 , 0, 0 > 0$
	Mar d To 1/2 and to 1/2 in
	mog d by in regim 2 is +
	$\mathcal{O}_{2} = \mathcal{O}_{1} \left(\frac{\cos^{2}\theta_{1} + \left(\frac{\varepsilon_{2}}{\varepsilon_{1}}\right)^{2} \sin^{2}\theta_{1}}{\varepsilon_{1}} \right)$
	を2= E1 Sih2 f (E1)2 (03 f)
	(< 2)
H	Capacitance #
-	A capacitor is a device that Stores electric potential cenergy

